

RESPONSE TO OFFICE ACTION**Serial No. 10/805,890****Page 2 of 9****IN THE SPECIFICATION**

Please replace paragraph [0006] with the following amended paragraph:

[0006] The disadvantages associated with the prior art are overcome by the present invention for etching materials with high dielectric constants (high K materials have a dielectric constant greater than 4.0) such as HfO_2 , ZrO_2 , Al_2O_3 , BST, PZK, ZrSiO_2 , HfSiO_2 , TaO_2 , and the like using a gas mixture comprising a halogen gas and reducing gas. In one embodiment of the invention, an etch gas (or mixture) comprising chlorine (Cl_2) and carbon monoxide (CO) is used for etching a hafnium-oxide films. In one example, the gas flow rates are in the range 20-300 sccm Cl_2 and about 2-200 sccm CO (i.e., a $[\text{Cl}_2]$ Cl_2/CO flow ratio (0.1-1):(1-0.1)), with a total chamber pressure in the range of 2-100 mTorr.

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